	1	1. DATE (YYMMDD)	Form Approved OMB No. 0704-					
	This revision described below has been authorized for the document listed. 95-01-25 Public reporting burden for this collection is estimated to average 2 hours per response, including the time for reviewing instructions							
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Budget, Paperwork F FORM TO EITHER (CONTRACTING OF	Public reporting burden for this collection is estimated to average 2 hours per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden, to Department of Defense, Washingtion Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington, VA 22202-4302, and to the Office of Management and Budget, Paperwork Reduction Project (0704-0188), Washington, DC 20503. PLEASE DO NOT RETURN YOUR COMPLETED FORM TO EITHER OF THESE ADDRESSED. RETURN COMPLETED FORM TO THE GOVERNMENT ISSUING CONTRACTING OFFICER FOR THE CONTRACT/ PROCURING ACTIVITY NUMBER LISTED IN ITEM 2 OF THIS FORM.							
4. ORIGINATOR			b. ADDRESS (Street, City, State Defense Electronics Supply	, ,	5. CAGE CODE 67268	6. NOR NO. 5962-R060-95		
a. TYPED NAME (Fi Last)	irst, Middle	e Initial,	1507 Wilmington Pike Dayton, OH 45444-5270		7. CAGE CODE 67268	8. DOCUMENT NO. 5962-91690		
9. TITLE OF DOCUMENT Microcircuit, Linear,			2-Bit A/D Converter with	10. REVISION L	ETTER	11. ECP NO.		
Microprocessor Int	terface, N	Ionolithic Silicon.		a. CURRENT	b. NEW	No registered users		
				С	D			
12. CONFIGURATIO	ON ITEM (OR SYSTEM) TO W	/HICH ECP APPLIES					
Revisions Revision I Rev statu: Sheet 10: Figure and 0 Revision	descripti date colu evel block s of shee e 1, Term 04". Chai level block	ion column; add "C umn; add "95-01-2 k; add "D". its; For sheets 1 au ninal connections; nge column for de ck; add "D".	nd 10, add "D". Terminal symbol columns, Char vice types "03 and 04" to device	nge column for devic	e types "01 and 02" to o	device types "01, 02,		
14. THIS SECTION	N FOR G	OVERNMENT US	SE ONLY					
a. (X one)	X		ument supplemented by the NO					
		1	ument must be received before	-				
			master document shall make a					
b. ACTIVITY AUTHO	ORIZED T	O APPROVE CHAN	IGE FOR GOVERNMENT	c. TYPED NAME Michael A. Frye	First, Middle Initial, Last)			
d. TITLE Chief, Microelectronics Branch			e. SIGNATURE Michael A. Frye		f. DATE SIGNED (YYMMDD) 95-01-25			
15a. ACTIVITY ACC DESC-ELDS	OMPLISH	HING REVISION	b. REVISION COMPLETED (Sig Sandra Rooney					

DD Form 1695, APR 92

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			ncluding the time for re ting and reviewing the collection of informatior ars Services, Directora 2-4302, and to the Offic	viewing instructions, collection of , including te for Information ce of Management and	2. PROCURING ACTIVITY NO.	
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4. ORIGINATOR	Defense	b. ADDRESS (Street, City, State, Zip Code) Defense Electronics Supply Center			6. NOR NO. 5962-R017-95	
a. TYPED NAME (First, Middle Initial, Last)		lmington Pike OH 45444-5270		7. CAGE CODE 67268	8. DOCUMENT NO. 5962-91690	
9. TITLE OF DOCUMENT Microcircuit	, Linear, 12-Bit A/D co	nverter with	10. REVISION LE	TTER	11. ECP NO. No	
microprocessor interface, Monolithic	Silicon.		a. CURRENT	b. NEW	registered users	
			В	С		
12. CONFIGURATION ITEM (OR SYST	EM) TO WHICH ECP AI	PPLIES				
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b. ACTIVITY AUTHORIZED TO APPRO DESC-ELDS				irst, Middle Initial, Last)		
d. TITLE Chief, Microelectronics Branch	e. SIGNATU Michael A.			f. DATE SIGNED (YYMMDD) 95-01-17		
15a. ACTIVITY ACCOMPLISHING REV DESC-ELDS	ISION b. REVISIO Sandra Ro	ON COMPLETED (Signation Doney	ature)	c. DATE SIGNED (YYMMDD) 95-01-17		

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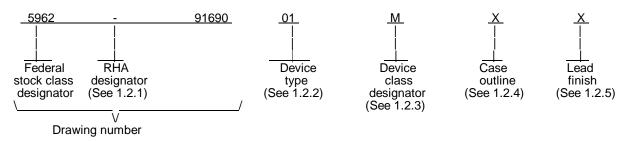
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DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

1. SCOPE

1.1 <u>Scope</u>. This drawing forms a part of a one part - part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes B, Q, and M) and space application (device classes S and V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of radiation hardness assurance (RHA) levels are reflected in the PIN.

1.2 <u>PIN</u>. The PIN shall be as shown in the following example:



1.2.1 <u>Radiation hardness assurance (RHA) designator</u>. Device classes M RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 <u>Device type(s)</u>. The device type(s) shall identify the circuit function as follows:

Device type	Generic num	nber Circuit function
01	674ZA	High performance, 12-bit A/D converter with microprocessor interface and S/H
02	674ZB	Medium performance, 12-bit A/D converter with microprocessor interface and S/H
03	674BT	12-bit A/D converter with microprocessor interface
04	674AT	12-bit A/D converter with microprocessor interface

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
Μ	Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883
Q or V	Certification and qualification to MIL-I-38535

1.2.4 <u>Case outline(s)</u>. The case outline(s) shall be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
X	GDIP1-T28 or CDIP2-T28	28	dual-in-line
3	CQCC1-N28	28	square chip carrier package

1.2.5 <u>Lead finish</u>. The lead finish shall be as specified in MIL-STD-883 (see 3.1 herein) for classes M or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

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1.3 Absolute maximum ratings. 1/

V _{CC} to digital common	
momentary short to V_{CC} Power dissipation (P _D): Device types 01 and 02 (T _A = +25°C) Device type 03 (T _A = +25°C) Lead temperature (soldering, 10 seconds) Storage temperature (T _J)	

1.4 Recommended operating conditions.

Logic supply voltage (V _{LOGIC})	+4.5 V dc to +5.5 V dc +11.4 V dc to +16.5 V dc
Negative supply voltage (V _{EE}) <u>2</u> / Ambient operating temperature range (T _A)	-11.4 V dc to -16.5 V dc -55° C to +125° C

2. APPLICABLE DOCUMENTS

2.1 <u>Government specifications, standards, bulletin, and handbook</u>. Unless otherwise specified, the following specifications, standards, bulletin, and handbook of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATIONS

MILITARY

MIL-I-38535

Integrated Circuits, Manufacturing, General Specification for.

0 V dc to +16.5 V dc 0 V dc to -16.5 V dc 0 V dc to +7 V dc -0.5 V dc to +1 V dc

-0.5 V dc to V_{LOGIC} + 0.5 V dc

Indefinite short to common

±1 V dc

±16.5 V dc ±24 V dc

1000 mW 470 mW +300° C

+175° C

48° C/W 60° C/W 50° C/W 48° C/W

-65° C to +150° C

See MIL-STD-1835

STANDARDS

MILITARY

MIL-STD-883	-	Test Methods and Procedures for Microelectronics.
MIL-STD-973	-	Configuration Management.
MIL-STD-1835	-	Microcircuit Case Outlines.

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

 $2/\dot{V}_{FF}$ is not required for operation of devices 01 and 02, and 04.

-

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BULLETIN

MILITARY

MIL-BUL-103 - List of Standardized Military Drawings (SMD's).

HANDBOOK

MILITARY

MIL-HDBK-780 - Standardized Military Drawings.

(Copies of the specifications, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

3.1 <u>Item requirements</u>. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535, the device manufacturer's Quality Management (QM) plan, and as specified herein.

3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-STD-883 (see 3.1 herein) for classes M and MIL-I-38535 for device classes Q and V and herein.

3.2.1 <u>Case outline(s)</u>. The case outline(s) shall be in accordance with 1.2.2 herein.

3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.

3.2.3 <u>Truth table</u>. The truth table shall be as specified on figure 2.

3.2.4 Block or logic diagram. The block or logic diagram shall be as specified on figure 3.

3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are described in table I.

3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes Q and V shall be in accordance with MIL-I-38535.

3.5.1 <u>Certification/compliance mark</u>. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes Q and V shall be a "QML" as required in MIL-I-38535.

3.6 <u>Certificate of compliance</u>. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.2 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.1 herein). The certificate of compliance submitted to DESC-ECS prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M the requirements of MIL-STD-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-I-38535 and the requirements herein.

3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing.

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Test	Symbol	Conditions $1/$ Group A Device Limits		mits	Unit		
		$\begin{array}{l} -55^{\circ}C \leq T_A \leq +1\overline{2}5^{\circ}C \\ V_{CC} = +15 \ V, \ V_{LOGIC} = +5 \ V, \\ unless \ otherwise \ specified \end{array}$	subgroups	type	Min	Max	
Power supply current from V _{LOGIC} <u>2</u> /	ILOGIC	Three-state outputs	1, 2, 3	01,02 04		+1.0	mA
				03		+7.0	
Power supply current from V _{CC 2} /	Icc		1, 2, 3	01,02 04		+9.0	
				03		+7.0	
Power supply current from V _{EE}	I _{EE}		1, 2, 3	03	-14		
Resolution			1	All	12		Bits
Integral linearity	ILE	Unipolar 10 V span Bipolar 20 V span	2, 3	All	-0.5	+0.5	LSB
error		Bipolai 20 V Spari		All	-1.0	+1.0	
Differential linearity error (minimum resolution for which no missing codes are guaranteed)	DLE		1, 2, 3	All	12		Bits
Unipolar offset voltage error	V _{IO}	10 V span	1	All	-2.0	+2.0	LSB
Unipolar offset voltage ddrift	▲V _{IO} ▲T	10 V span Using internal reference	2, 3	All	-1.0	+1.0	
Bipolar zero offset error	BZ	20 V span	1	01,02 04	-4.0	+4.0]
				03	-3.0	+3.0	
Bipolar zero offset drift	▲B _Z	20 V span Using internal reference	2, 3	02,03 04	-2.0	+2.0]
	▲T			01	-1.0	+1.0	
Gain error	Α _E	Bipolar 20 V span 50Ω resistor from	1	01,02 04			%FSR
		REF OUT to REF IN		03			

Α **MICROCIRCUIT DRAWING** DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444 **REVISION LEVEL**

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В

Test	Symbol		Group A subgroups	Device	Li	mits	Unit
		$V_{CC} = +15 \text{ V}, V_{LOGIC} = +5 \text{ V},$ unless otherwise specified	subgroups	type	Min	Max	
Gain error drift	▲A _E	Bipolar 20V span	2, 3	01		12.5	ppm/°C
	 ▲T	Using internal reference		02,04		25.0	
				03		17.5	
Power supply sensitivity to V _{CC} <u>3</u> / <u>4</u> /	+PSS1		1, 2, 3	All	-1.0	+1.0	LSB
Power supply sensitivity to V _{LOGIC} <u>3</u> / <u>5</u> /	+PSS2		1, 2, 3	All	-0.5	+0.5	
Power supply sensitivity to V _{EE} <u>3</u> / <u>6</u> /	-PSS3		1, 2, 3	03	-1.0	+1.0	
Input impedence 2/	Z _{IN}	Z _{IN} 10 V span	1, 2, 3	01,02 04	3.75	6.25	kΩ
				03	3.0	7.0	
		20 V span	1, 2, 3	01,02 04	15	25	
				03	6	14	
Internal reference voltage <u>7</u>	V _{REF}	I _{REFOUT} = 2 mA	1, 2, 3	01,02 04	9.97	10.03	V
				03	9.9	10.1	
Logic input high voltage (CE, CS, 12/8, R/C, A _O) <u>2/8/</u>	V _{IH}	Logic "1"	1, 2, 3	All	+2.0	+5.5	V
Logic input low voltage (CE, CS, 12/8, R/C, A _O) <u>2/8/</u>	VIL	Logic "0"	1, 2, 3	All	-0.5	+0.8	V

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	TAE	BLE I. Electrical performan	nce charad	<u>cteristics</u> - C	Continued.			
Test	Symbol	Conditions <u>1</u> / -55°C ≤ T _A ≤+125°0	С	Group A subgroup		Li	mits	Unit
		$\begin{array}{r} -55^{\circ}C \leq T_A \leq +1\overline{2}5^{\circ}C \\ V_{CC} = +15 \text{ V}, V_{LOGIC} = +5 \\ \text{unless otherwise specified} \end{array}$	V,	•		Min	Max	
Logic input current 2/	I _{IN(LOG)}	0 to +5.5 V input		1, 2, 3	01,02		+1.0	μA
<u></u>					04	-20	+20	
		0 to + 5.0 V input			03	-10	+10	
Logic low output voltage <u>2</u> / (DB11-DB0)	V _{OL}	Logic "0" I _{sink} = 1.6 mA		1, 2, 3	All		+0.4	V
Logic high output voltage <u>2</u> / (DB11-DB0)	V _{OH}	Logic "1" I _{source} = 500 µA		1, 2, 3	All	+2.4		V
Three-state output	Ι _Ζ	High-Z state		1, 2, 3	01,02	-5.0	+5.0	μA
leakage current		(DB11 - DB0 only) V _{applied} = 5.0 V			03	-10	+10	
					04	-20	+20	
Functional tests 2/		See section 4.4.1b		7, 8	All			
Low R/C pulse width <u>9</u> /	t _{HRL}	See figure 4		9, 10, 11	All	50		ns
STS delay from R/C	^t DS				01,02 04		200	
					03		225	
Data valid after R/C low <u>11</u> /	^t HDR				All	25		
STS delay after data valid	^t HS				01,02 04	300	1000	
					03	30	600	_
High R/C pulse width <u>9</u> /	t _{HRH}				All	150		
Data access time <u>12</u> /	^t DDR						150	
See footnotes at end of t	able.							
STAN MICROCIF	NDARDI RCUIT D		SIZ A				59	62-91690
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TABLE I. Electrical performance characteristics - Continued.							
Test	Symbol	Conditions <u>1</u> / -55°C ≤ T _A ≤+125°C	Group A subgroups	Device type	Li	imits	Unit
		$V_{CC} = +15 \text{ V}, V_{LOGIC} = +5 \text{ V},$ unless otherwise specified		1940	Min	Max	1
STS delay from CE	t _{DSC}	See figure 5	1, 2, 3	01,02		200	ns
<u>10</u> /				03		225	
CE pulse width <u>9</u> /	t _{HEC}			All	50		
CS to CE setup	t _{SSC}				50		
Conversion time	^t C	8-bit cycle, see figure 5	9, 10, 11	All	6	10	μs
<u>13</u> /		12-bit cycle, see figure 5			9	15	
CS low during CE	tHSC	See figure 5	9, 10, 11	All	50		
R/\overline{C} to CE setup	t _{SRC}				50		
R/C low during CE high	^t HRC				50		
A ₀ to CE setup	t _{SAC}				0		
A ₀ valid during CE high	^t HAC				50		
Access time (from CE) <u>12</u> /	t _{DD}	See figure 6	9, 10, 11	All		150	ns
Data valid after CE low <u>11</u> /	t _{HD}			01,02 04	25]
			11	03	15		1
			9, 10		25		<u>]</u>
Output float delay <u>11</u> /	t _{HL}		9, 10, 11	All		150	
CS to CE setup	t _{SSR}			All	50		
R/C to CE setup	t _{SRR}			All	0		
Sample and hold <u>14</u> / acquisition time	t _{acq}	$T_A = +25^{\circ}C$	9	01,02 04	1.2	2.0	μs
A ₀ to CE setup	t _{SAR}	See figure 6	9, 10, 11	All	50	Γ	ns

See footnotes at end of table.

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	TAB	LE I. Electrical performan	ce chara	cteristics - Co	ntinued.			
Test	Symbol	Conditions <u>1</u> / -55°C ≤ T _A ≤+125°C	2	Group A subgroups	Device	Li	mits	Unit
		$V_{CC} = +15 \text{ V}, V_{LOGIC} = +5$ unless otherwise specified	V,	subgroups	type	Min	Max	
CS valid after CE low	^t HSR	See figure 6		9, 10, 11	All	0		ns
R/C high after CE low	^t HRR				All	0		
A ₀ valid after CE low	t _{HAR}				All	50		
 1/ 12/8 connected to V_{LOGIC}, Ao and CS at logic "0", CE at logic "1". 10 V unipolar: 50Ω registor pin 8 to pin 10, 50Ω resistor pin 12 to ground. Analog input connected to pin 13. 20 V bipolar: 50Ω resistor pin 8 to pin 12, 50 resistor pin 8 to pin 10. Analog input connected to pin 13. 2/ Device types are tested to the conditions stated in table I, but are guaranteed to the specified limits for the following variations in the supply voltage ranges. V_{LOGIC} = +5 V to ±5%, V_{CC} = +12 V ±5% and +15V to ±10%, V_{EE} = -12 V ±5% and -15 V ±10%. (V_{EE} not required for operation of devices 01, 02, and 04). For device type 03, V_{LOGIC} = +5 V to ±10%. 3/ Maximum change in full scale calibration due to supply voltage shifts. Full scale calibration to be measured at minimum and maximum voltage settings for each individual supply. 4/ +13.5 V ≤ V_{CC} ≤ +16.5 V, V_{LOGIC} = 5 V, V_{EE} = -15 V and +11.4 V ≤ V_{CC} ≤ +12.6 V, V_{LOGIC} = 5 V, V_{EE} = -12 V. V_{EE} not required for operation of devices 01, 02, and 04). 5/ 4.5 V ≤ V_{LOGIC} ≤ 5.5 V, V_{CC} = 15V, V_{EE} = -15V. (V_{EE} not required for operation of devices 01, 02, and 04). 6/ -16.5 V ≤ V_{EE} ≤ -13.5 V, V_{LOGIC} = 5 V, V_{CC} = +15 V and -12.6 V ≤ V_{EE} ≤ -11.4 V, V_{LOGIC} = 5 V, V_{CC} = +12 V. 								
 <u>7</u>/ Reference should be bu during conversion. <u>8</u>/ For devices types 01, 02 digital common. 						-		
<u>9</u> / Pulse width is measured	d at the Sch	ottky TTL input logic thre	shold vo	ltage (1.3 V).				
<u>10</u> / t _{DS} and t _{DSC} are meas logic threshold voltage (* is applied to STS.	sured from t 1.3 V) to wh	he point when the input s ien the STS output reach	signal cro es 2.4 V.	osses the Sch No external	ottky TTL loading			
<u>11/</u> t _{HDR} , t _{HD} , and t _{HL} are TTL logic threshold volta of its final high impedanc for both logic one to "hig shown on figure 7.	measured f age (1.3 V), ce output vo h Z" and log	from the point when the in to when the output voltage oltage. Each individual da gic zero to "high Z" transi	nput sign ge has m ata bit (D tions. E>	al crosses the oved 0.5 V in BO - DB11) i kternal loading	e Schottky the directions measure g is as	on d		
<u>12</u> / t _{DDR} and t _{DD} are meas logic threshold voltage (0.4 V for a logic zero. E logic zero transitions. E	ach individi	the point when the input s hen the output crosses ei ıal data bit (DBO - DB11) ing is as shown on figure	is meas	osses the Sch V for a logic c ured for both	ottky TTL ne, or "high Z" to			
<u>13</u> / t _C is measured as the t when it crosses the 1.0 \	ime from w / level going	hen the STS line crosses g negative. No external lo	the 1.0 \ bading is	/ level, going applied to S	positive, to S.)		
<u>14</u> / Guaranteed by design.								
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					-			

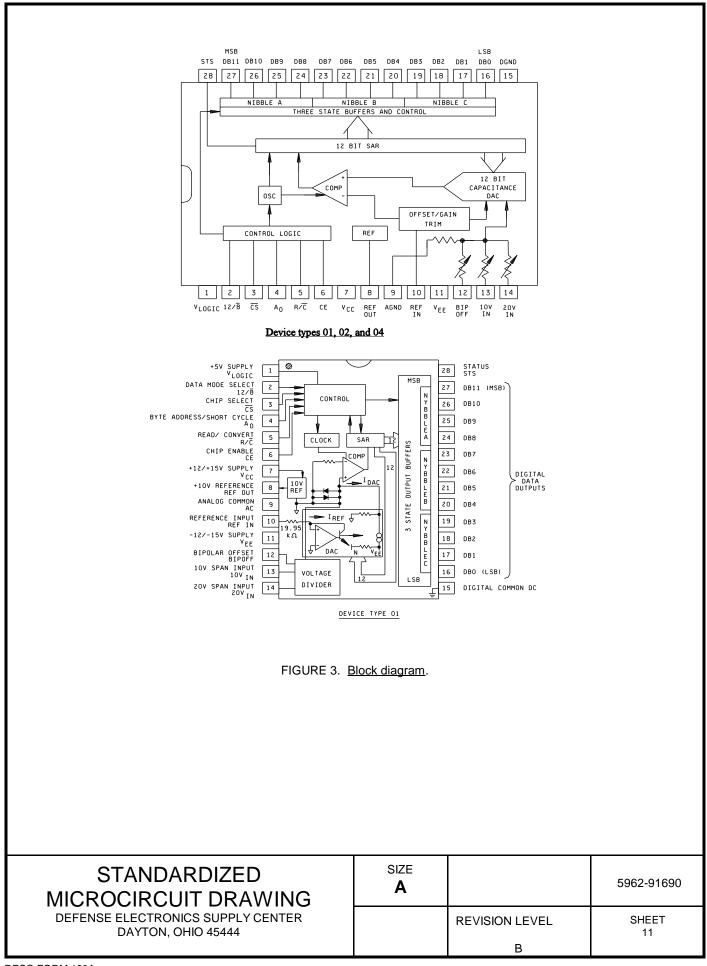
Device types	01 and 02	03 and 04
Case outlines	X and 3	X
Terminal number	Terminal symbol	
1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28	+5 V supply (V_{LOGIC}) Data mode select (12/8) Chip select (\overline{CS}) Byte address/short cycle (A_O) Read/convert (R/\overline{C}) Chip enable (CE) +12 V/+15 V supply (V_{CC}) +10 V reference (REF OUT) Analog common (AGND) Reference input (REF IN) -12 V/-15 V supply (V_{EE}) Bipolar offset (BIP OFF) 10 V span input (10 V _{IN}) 20 V span input (20 V _{IN}) Digital common (DGND) DB0 (LSB) DB1 DB2 DB3 DB4 DB5 DB6 DB7 DB8 DB9 DB10 DB11 (MSB) Status (STS)	+5 V supply (V_{LOGIC}) Data mode select (12/8) Chip select (\overline{CS}) Byte address/short cycle (A_O) Read/convert (R/\overline{C}) Chip enable (CE) +12 V/+15 V supply (V_{CC}) +10 V reference (REF OUT) Analog common (AGND) Reference input (REF IN) -12 V/-15 V supply (V_{EE}) Bipolar offset (BIP OFF) 10 V span input (10 V _{IN}) 20 V span input (20 V _{IN}) Digital common (DGND) DB0 (LSB) DB1 DB2 DB3 DB4 DB5 DB6 DB7 DB8 DB9 DB10 DB11 (MSB) Status (STS)

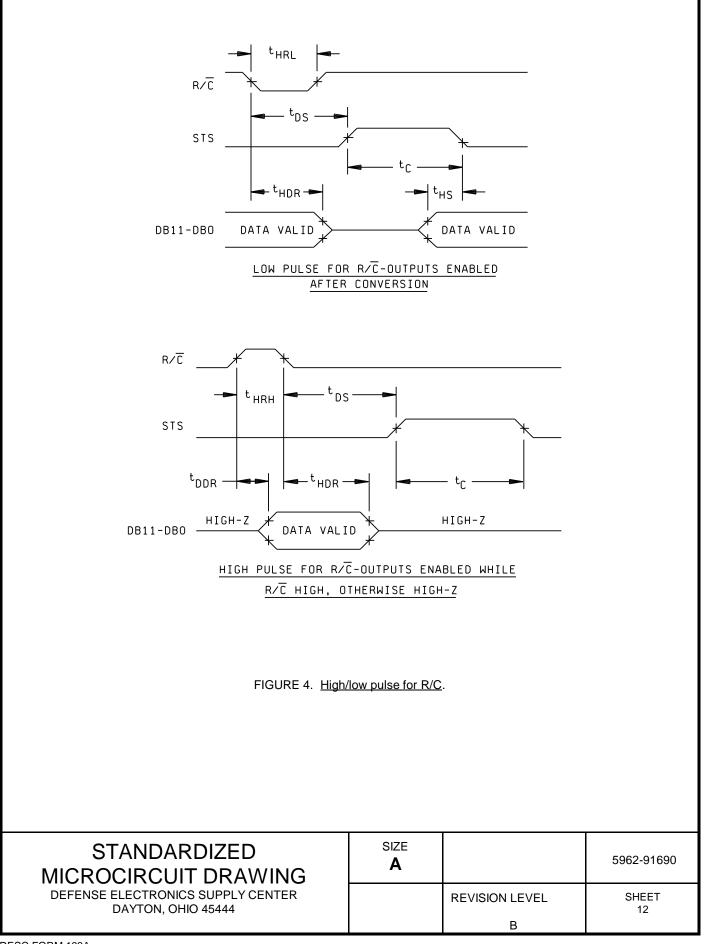
FIGURE 1. Terminal connections.

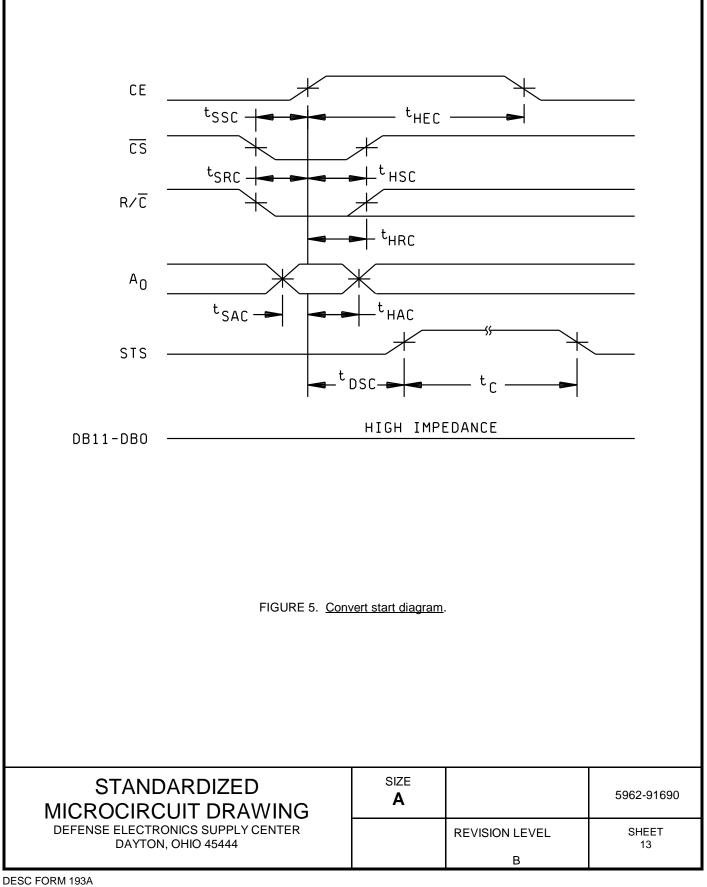
CE	CS	R/C	12/8	A _O	Operation
0	X	X	X	X	None
X	1	X	X	X	None
1	0	0	X	0	Initiate 12-bit conversion
	0	0	X	1	Initiate 8-bit conversion
1	0	1	1	х	Enable 12-bit parallel output
1	0	1	0	0	Enable 8 most significant bits
	0	1	0	1	Enable 4 LSBs + 4 trailing zeros

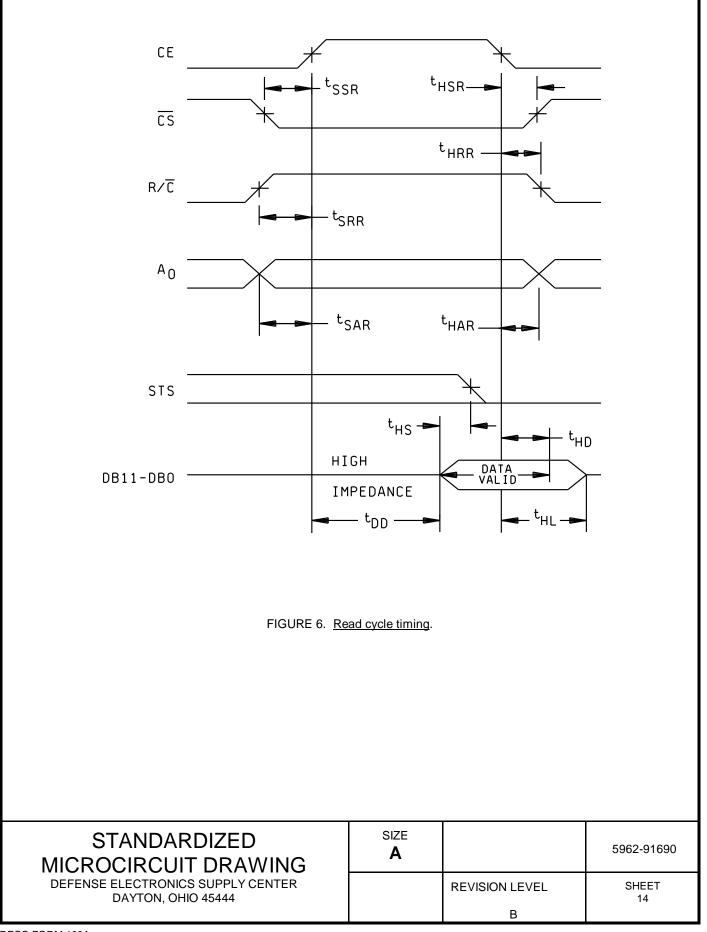
FIGURE 2. Truth table.

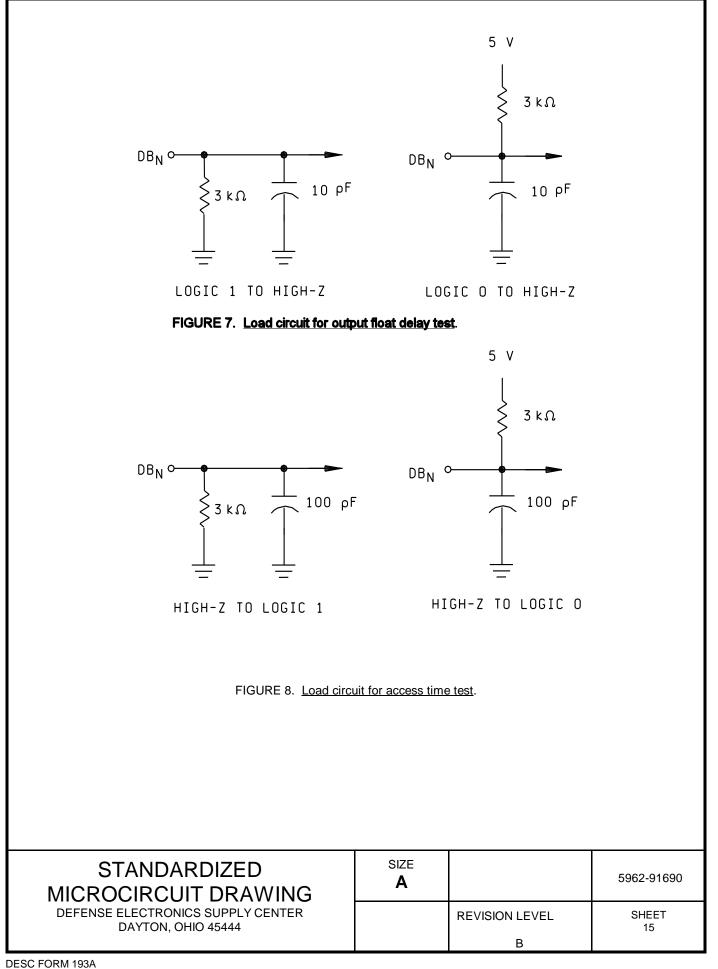
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3.8 <u>Notification of change for device class M</u>. For device class M, DESC, DESC's agent, and the change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.

3.9 <u>Verification and review for device class M</u>. For device class M, DESC, DESC's agent and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 <u>Microcircuit group assignment for device classes M</u>. Device classes M devices covered by this drawing shall be in microcuiruit group number 93 (see MIL-M-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

4.1 <u>Sampling and inspection</u>. For device class M, sampling and inspection procedures shall be in accordance with MIL-STD-883 (see 3.1 herein). For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 and the device manufacturer's QM plan.

4.2 <u>Screening</u>. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

4.2.1 Additional criteria for device classes M.

- a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
- b. Interim and final electrical test parameters shall be as specified in table II herein.

4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-M-38535. The burn-in test shall be submitted to DESC-ECS with the certificate of compliance and shall be under the control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.

4.3 Qualification inspection.

4.3.1 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 <u>Conformance inspection</u>. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4). Technology conformance inspection for classes Q and V shall be in acccordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.

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TABLE II. Electrical test requirements.

	-	-	
Test requirements	Subgroups (in accordance with MIL-STD-883, TM 5005, table I)	Subgroups (in accordance with MIL-I-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1,2,3, <u>1</u> /	1,2,3 <u>1</u> /	1,2,3, <u>2</u> /
Group A test requirements (see 4.4)	1,2,3,7 8,9,10,11 <u>2</u> /	1,2,3,7, 8,9,10,11 <u>2</u> /	1,2,3,7, 8,9,10,11 <u>2</u> /
Group C end-point electrical parameters (see 4.4)	1	1	1
Group D end-point electrical parameters (see 4.4)	1	1	1

<u>1</u>/ PDA applies to subgroup 1.

2/ PDA applies to subgroups 1 and 7.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).
- c. Subgroups 4, 5, and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
- 4.4.2 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shallbe as specified in table II herein.
- 4.4.2.1 Additional criteria for device classes M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
 - b. $T_A = +125^{\circ} C$, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 <u>Additional criteria for device classes Q and V</u>. The steady-state life test duration, test condition and test temperature or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB, in accordance with MIL-I-38535, and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.

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- a. End-point electrical parameters shall be as specified in table II herein.
- b. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-M-38535, appendix A, for RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-I-38535 for RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at $T_A = +25^{\circ} C \pm 5$ percent, after exposure, to the subgroups specified in table II herein.

c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.1.2 <u>Substitutability</u>. Device class Q devices will replace device class M devices.

6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

6.3 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-ECS, telephone (513) 296-6047.

6.4 <u>Comments</u>. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone (513) 296-5377.

6.5 Abbreviations, symbols, and definitions.

6.6 <u>One part - one part number system</u>. The one part - one part number system described below has been developed to allow for transitions between identical generic devices covered by the threemajor microcircuit requirements documents (MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The three military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all three documents, the OEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

Military documentation format	Example PIN under new system	Manufacturing source listing	Document listing
New MIL-H-38534 Standardized Military Drawings	5962-XXXXXXX(H or K)YY	QML-38534	MIL-BUL-103
New MIL-I-38535 Standardized Military Drawings	5962-XXXXXXX(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standardized Military Drawings	5962-XXXXXXX(M)YY	MIL-BUL-103	MIL-BUL-103

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6.7 Sources of supply.

6.7.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-ECS and have agreed to this drawing.

6.7.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-ECS.

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STANDARDIZED MILITARY DRAWING SOURCE APPROVAL BULLETIN

DATE: 94-09-01

Approved sources of supply for SMD 5962-91690 are listed below for immediate acquisition only and shall be added to MIL-BUL-103 during the next revision. MIL-BUL-103 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DESC-ECS. This bulletin is superseded by the next dated revision of MIL-BUL-103.

Standard microcircuit drawing PIN	Vendor CAGE number	Vendor similar PIN <u>1</u> /	Replacement military specification PIN
5962-9169001MXX	0H9K9	HADC674ZAMD/883	M38510/14005BXX
5962-9169001M3X	0H9K9	HADC674ZAMC/883	
5962-9169002MXX	0H9K9	HADC674ZBMD/883	M38510/14006BXX
5962-9169002M3X	0H9K9	HADC674ZBMC/883	
5962-9169003MXX	24355	AD674BTD/883B	M38510/14006BXX
5962-9169003M3X	24355	AD674BTE/883B	
5962-9169004MXX	33256	SP674AT/B	M38510/14006BXX

<u>1</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number	Vendor name and address
0Н9К9	Signal Processing Technologies, Incorporated 1510 Quail Lake Loop Colorado Springs, CO 80906
24355	Analog Devices 804 Woburn Street Wilmington, MA 01887
33256	Sipex Corporation 22 Linnell Circle Billerica, MA 01821-3985

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.